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ABSTRACT OF THE DISCLOSURE
SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREFOR

To provide a semiconductor device in which reduction of a variation in resistance value of a polycrystalline silicon film resistor is promoted. In a semiconductor device and a manufacturing method therefor according to the present invention, when the polycrystalline silicon film resistor is formed, a construction thereof is achieved by determining an implantation amount of an impurity implanted into the polycrystalline silicon film resistor through a novel technique to constitute a semiconductor integrated circuit device superior in performance.

Fig. 1